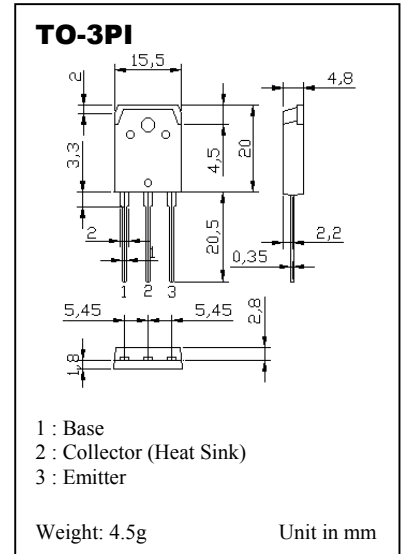


NPN TRIPLE DIFFUSED TRANSISTOR

...designed for high power amplifier application.
 ...complementary to PMB688.

MAXIMUM RATINGS (Ta = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V _{CB0}	120	V
Collector Emitter Voltage	V _{CEO}	120	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	10	A
Base Current	I _B	1	A
Collector Power Dissipation T _c = 25 °C	P _C	80	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



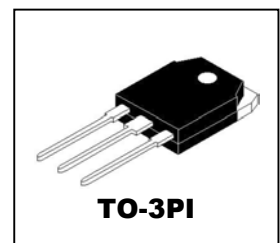
ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 120V, I _E = 0	-	-	10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V, I _B = 0	-	-	10	μA
Collector Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 50mA, I _B = 0	120	-	-	V
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 1A	55	-	160	-
Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C = 5A, I _B = 0.5A	-	-	2.5	V
Base Emitter Voltage	V _{BE}	V _{CE} = 5V, I _C = 5A	-	-	1.5	V
Transition Frequency	f _T	V _{CE} = 5V, I _C = 1A	-	12	-	MHz
Collector Output Capacitance	C _{ob}	V _{CE} = 10V, I _E = 0, f = 1MHz	-	170	-	pF

**NPN TRIPLE
 DIFFUSED
 TRANSISTOR**

CLASSIFICATIONS OF h_{FE}

Rank	R	O
Range	55 to 110	80 to 160



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